





### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C	
-50V	$10\Omega @ V_{GS} = -5V$	-130mA	

### **Description**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

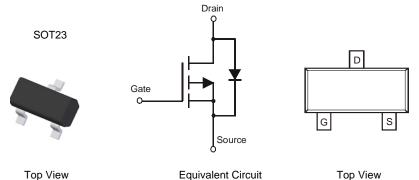
- · General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (Lead Free Plating) Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



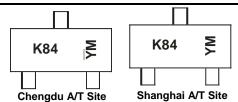
### Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
BSS84-7-F	Commercial	SOT23	3000/Tape & Reel
BSS84Q-7-F	Automotive	SOT23	3000/Tape & Reel
BSS84-13-F	Commercial	SOT23	10000/Tape & Reel
BSS84Q-13-F	Automotive	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

### **Marking Information**



K84 = Product Type Marking Code

 $\underline{YM}$  = Date Code Marking for SAT (Shanghai Assembly/ Test site)  $\underline{YM}$  = Date Code Marking for CAT (Chengdu Assembly/ Test site)  $\underline{Y}$  or  $\underline{Y}$  = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004		2011	2012	2013	2014	2015	2016	2017
Code	J	K	L	М	N	Р	R		Υ	Z	Α	В	С	D	Е
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Month	Jan	Fel	ו ס	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		N	D



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	-50	V
Drain-Gate Voltage $R_{GS} \le 20K\Omega$		$V_{DGR}$	-50	V
Gate-Source Voltage	Continuous	V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Continuous	I <sub>D</sub>	-130	mA
Pulsed Drain Current		I <sub>DM</sub>	-1.2	A

# **Thermal Characteristics** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	$P_{D}$	300	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-50		_	V	$V_{GS} = 0V, I_D = -250\mu A$	
				-1	μA	$V_{DS} = -50V$ , $V_{GS} = 0V$ , $T_{J} = +25$ °C	
Zero Gate Voltage Drain Current	$I_{DSS}$	_	_	-2	μΑ	$V_{DS} = -50V$ , $V_{GS} = 0V$ , $T_{J} = +125$ °C	
			_	-100	nA	$V_{DS} = -25V$ , $V_{GS} = 0V$ , $T_{J} = +25$ °C	
Gate-Body Leakage	I <sub>GSS</sub>		1	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.8	-	-2.0	V	$V_{DS} = V_{GS}$ , $I_D = -1mA$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)		1	10	Ω	$V_{GS} = -5V, I_D = -0.100A$	
Forward Transconductance	<b>g</b> FS	0.05	_	_	S	$V_{DS} = -25V, I_D = -0.1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C <sub>iss</sub>		_	45	pF		
Output Capacitance	Coss		1	25	pF	$V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	Crss			12	pF	1	
SWITCHING CHARACTERISTICS (Note 7)							
Turn-On Delay Time	t <sub>D(ON)</sub>		10		ns	$V_{DD} = -30V$ , $I_D = -0.27A$ ,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	18	_	ns	$R_{GEN} = 50\Omega$ , $V_{GS} = -10V$	

Notes:

- 5. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.
- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing



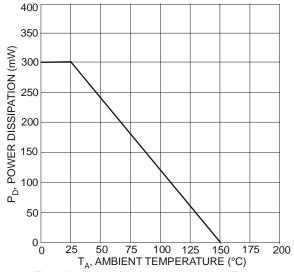
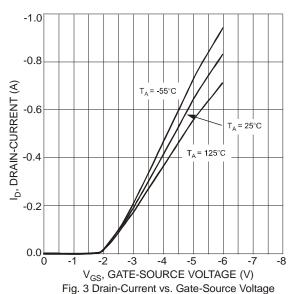
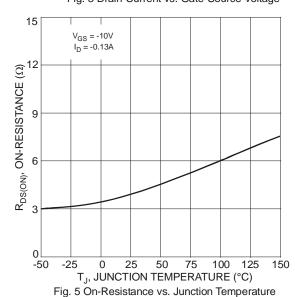


Fig. 1 Max Power Dissipation vs. Ambient Temperature





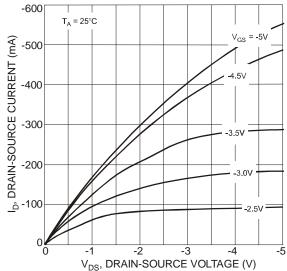


Fig. 2 Drain-Source Current vs. Drain-Source Voltage

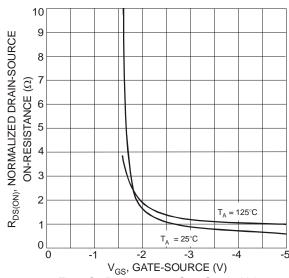


Fig. 4 On-Resistance vs. Gate-Source Voltage

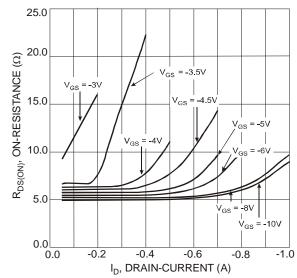
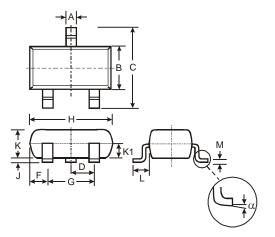


Fig. 6 On-Resistance vs. Drain-Current



# **Package Outline Dimensions**

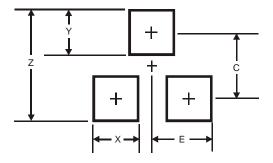
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
M	0.085	0.18	0.11					
α	0°	8°	-					
All Dimensions in mm								

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
С	2.0
Е	1.35

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